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Stocking Distributor

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[VS-100BGQ030](#)

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sales@integrated-circuit.com

International IOR Rectifier

100BGQ030
100BGQ030J

SCHOTTKY RECTIFIER

100 Amp

Major Ratings and Characteristics

Characteristics	100BGQ030	Units
I _{F(AV)} Rectangular waveform @T _C	100	A
	110	°C
I _{DC} Maximum	141	A
V _{RRM}	30	V
I _{FSM} @tp=5µs sine	4500	A
V _F @100Apk typical @T _J	0.48	V
	150	°C
T _J range	-55 to 150	°C

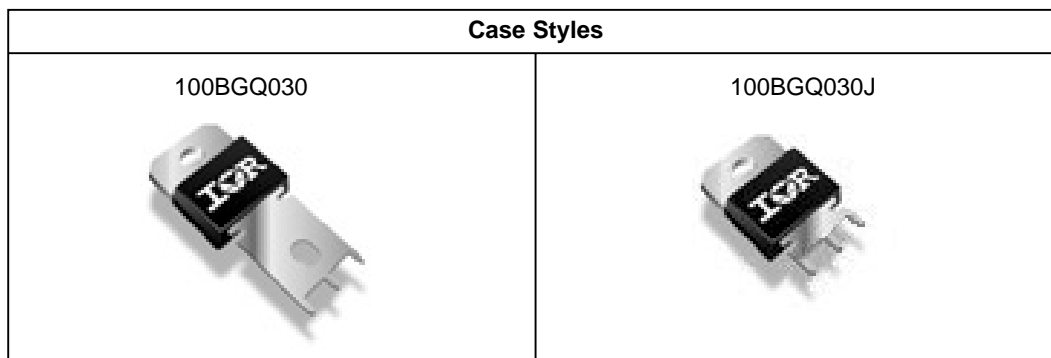
Description/ Features

The 100BGQ030 Schottky rectifier has been optimized for ultra low forward voltage drop specifically for low voltage output in high current AC/DC power supplies.

The proprietary barrier technology allows for reliable operation up to 150°C junction temperature. Typical applications are in switching power supplies, converters, reverse battery protection, and redundant power subsystems.

- 150°C T_J operation
- High Frequency Operation
- Ultra low forward voltage drop
- Continuous High Current operation
- Guard ring for enhanced ruggedness and long term reliability
- **PowIRtab™ package**

Case Styles



100BGQ030, 100BGQ030J

Bulletin PD-20996 rev. E 12/02

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Voltage Ratings

Part number	100BGQ030
V _R Max. DC Reverse Voltage (V)	30
V _{RWM} Max. Working Peak Reverse Voltage (V)	

Absolute Maximum Ratings

Parameters	100BGQ	Units	Conditions
I _{F(AV)} Max. Average Forward Current	100	A	50% duty cycle @ T _C = 110°C, rectangular waveform
I _{F(RMS)} RMS Forward Current	141	A	T _C = 107°C
I _{FSM} Max. Peak One Cycle Non-Repetitive Surge Current	4500	A	5µs Sine or 3µs Rect. pulse
	850		10ms Sine or 6ms Rect. pulse
E _{AS} Non-Repetitive Avalanche Energy	36	mJ	T _J = 25°C, I _{AS} = 8 Amps, L = 1.12 mH
I _{AR} Repetitive Avalanche Current	8	A	Current decaying linearly to zero in 1µsec Frequency limited by T _J max. V _A = 1.5 × V _R typical

Electrical Specifications

Parameters	100BGQ		Units	Conditions	
	Typ.	Max.			
V _{FM} Forward Voltage Drop (1) (2)	0.46	0.48	V	@ 50A	T _J = 25°C
	0.55	0.58	V	@ 100A	
	0.35	0.37	V	@ 50A	T _J = 150°C
	0.48	0.51	V	@ 100A	
I _{RM} Reverse Leakage Current (1)	0.6	2.4	mA	T _J = 25°C	V _R = rated V _R
	260	460	mA	T _J = 125°C	
	80	160	mA	T _J = 125°C	V _R = 15V
	800	1100	mA	T _J = 150°C	V _R = 30V
V _{F(TO)} Threshold Voltage	0.252		V	T _J = T _J max.	
r _t Forward Slope Resistance	2.4		mΩ		
C _T Max. Junction Capacitance	3800		pF	V _R = 5V _{DC} , (test signal range 100Khz to 1Mhz) 25°C	
L _S Typical Series Inductance	3.5		nH	Measured from tab to mounting plane	
dv/dt Max. Voltage Rate of Change (Rated V _R)	10000		V/µs		

(1) Pulse Width < 300µs, Duty Cycle < 2%

 (2) V_{FM} = V_{F(TO)} + r_t × I_F
Thermal-Mechanical Specifications

Parameters	100BGQ	Units	Conditions
T _J Max. Junction Temperature Range	-55 to 150	°C	
T _{stg} Max. Storage Temperature Range	-55 to 150	°C	
R _{thJC} Max. Thermal Resistance Junction to Case	0.50	°C/W	DC operation
R _{thCS} Typical Thermal Resistance, Case to Heatsink	0.20	°C/W	Mounting surface, smooth and greased
wt Approximate Weight	5(0.18)	g(oz.)	
T Mounting Torque	Min.	1.2(10)	N*m (lbf-in)
	Max.	2.4(20)	
Case Style	PowIRtab™		

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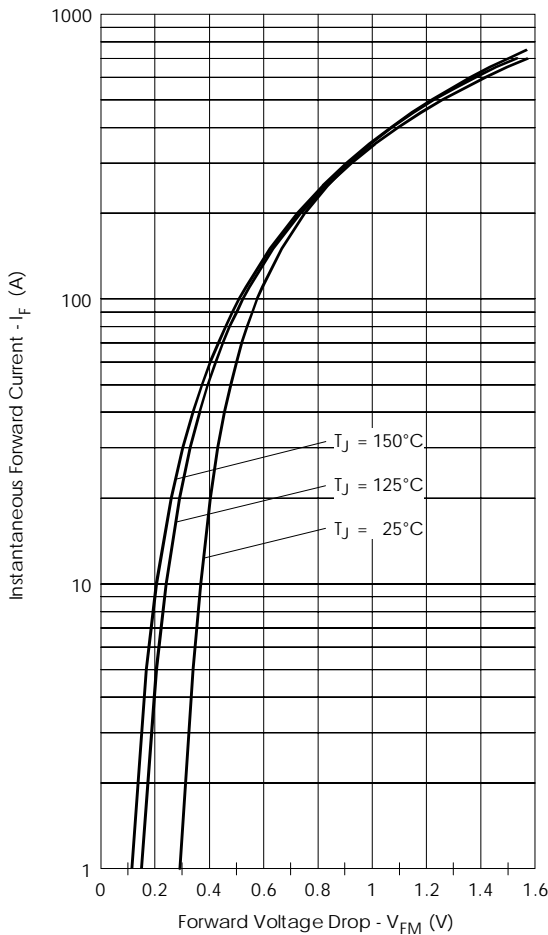


Fig. 1 - Maximum Forward Voltage Drop Characteristics

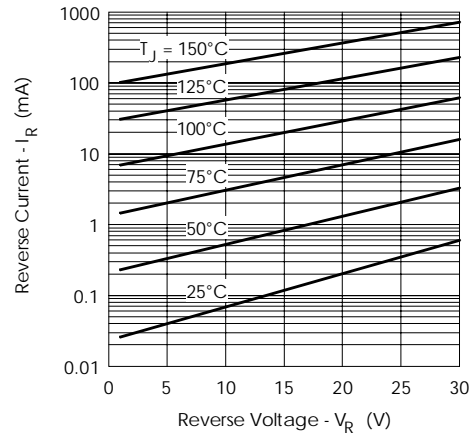


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

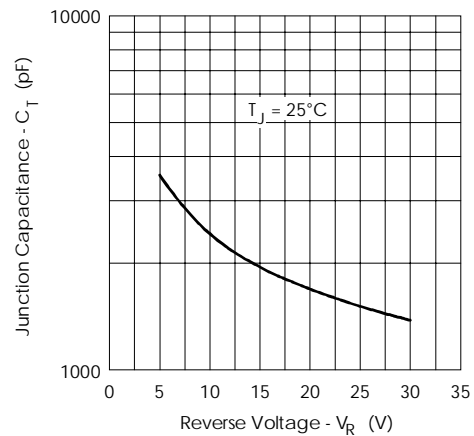


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

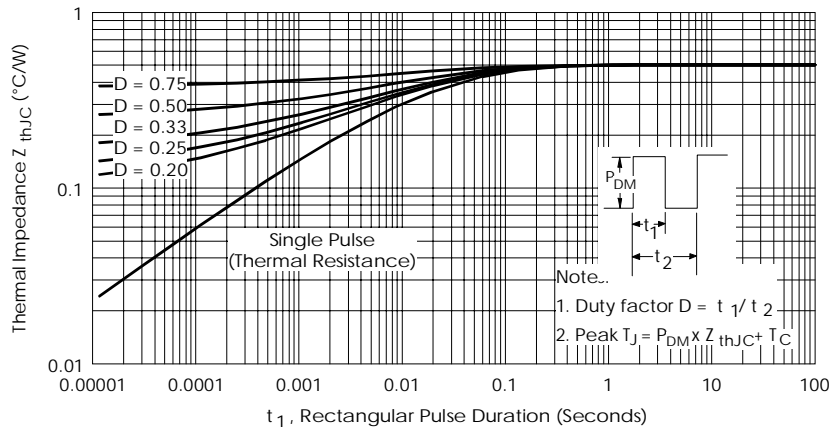


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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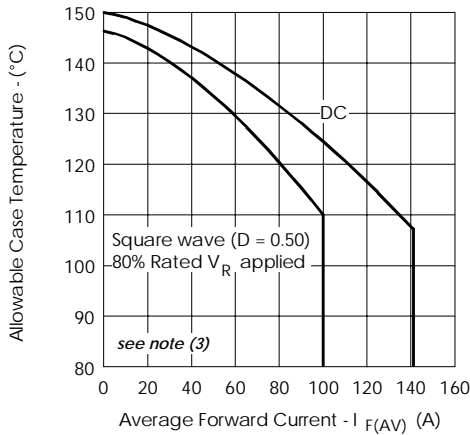


Fig.5- Maximum Allowable Case Temperature Vs. Average Forward Current

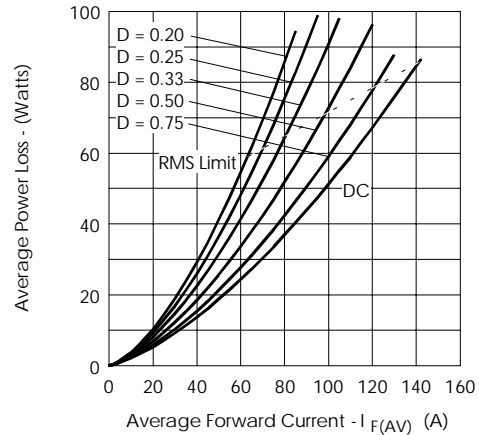


Fig.6- Forward Power Loss Characteristics

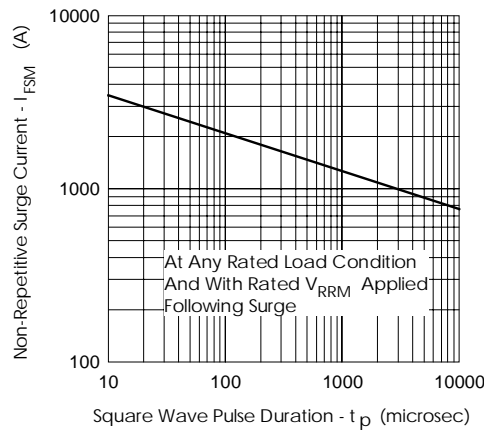


Fig.7- Maximum Non-Repetitive Surge Current

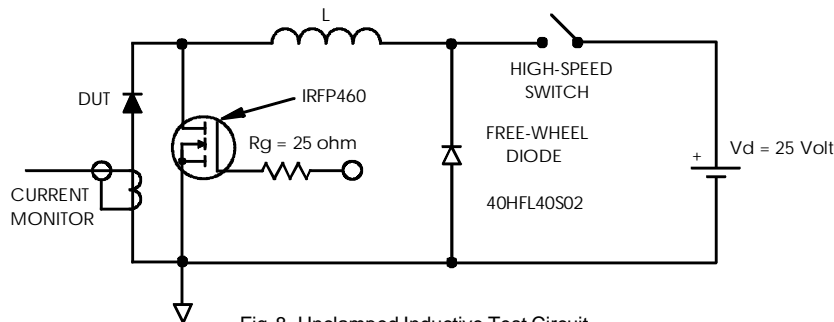


Fig.8- Unclamped Inductive Test Circuit

(3) Formula used: $T_c = T_j - (P_d + P_{d_{REV}}) \times R_{thJC}$;

P_d = Forward Power Loss = $I_{F(AV)} \times V_{FM} @ (I_{F(AV)}/D)$ (see Fig. 6);

$P_{d_{REV}}$ = Inverse Power Loss = $V_{R1} \times I_R (1 - D)$; $I_R @ V_{R1} = 80\%$ rated V_R

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Ordering Information Table

Device Code	100	BGQ	030	J
	①	②	③	④
1	- Current Rating			
2	- Essential Part Number			
3	- Voltage code: Code = V_{RRM}			
4	- none = PowIRtab™ standard			
	J = Short Lead Version			

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*****
This model has been developed by
Wizard SPICE MODEL GENERATOR(1999)
(International Rectifier Corporation)
contains Proprietary Information

*****
SPICE Model Diode is composed by a
simple diode plus paralalled VCG2T
*****

.SUBCKT 100bgq30 ANO CAT
D1 ANO 1 DMOD (0.24359)
*Define diode model
.MODEL DMOD D(IS=1.07823961851333E-04A,N=1.0394338412755,BV=30V,
+IBV=0.125061622097042A,RS=0.000316667,CJO=2.88578786999339E-08,
+VJ=1.30385147429609,XTI=2,EG=0.697469117594151)
*****
*Implementation of VCG2T
VX 1 2 DC 0V
R1 2 CAT TRES 1E-6
.MODEL TRES RES(R=1,TC1=6.48759701319255)
GP1 ANO CAT VALUE={-ABS(I(VX))*(EXP((( -2.690102E-03/
6.487597)*(V(2,CAT)*1E6)/(I(VX)+1E-6)-1)))+1}*9.995116E-02*ABS(V(ANO,CAT)))-1}

*****
.ENDS100bgq30

Thermal Model Subcircuit
.SUBCKT 100bgq30T 5 1
CTHERM1 5 4 3.02E+3
CTHERM2 4 3 4.96E+1
CTHERM3 3 2 3.84E+4
CTHERM4 2 1 3.02E+6

R THERM1 5 4 1.02E-1
R THERM2 4 3 3.83E-1
R THERM3 3 2 6.09E-2
R THERM4 2 1 1.00E-5

.ENDS 100bgq30T

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Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

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Visit us at www.irf.com for sales contact information. 12/02